

ABSTRACT

A semiconductor device 1000 may include a protective insulation layer 50, a pad opening section 60 provided in the protective insulation layer 50, and a wiring layer which the pad opening section reaches. First and second wiring layers 30 and 32 are provided at levels below the wiring layer 40 which the pad opening section reaches. The first and second wiring layers 30 and 32 provided at levels below the wiring layer 40 which the pad opening section reaches are formed outside a region of the pad opening section 60 as viewed in a plan view.

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